

SEMICONDUCTOR TECHNICAL DATA

KTA1658 EPITAXIAL PLANAR PNP TRANSISTOR

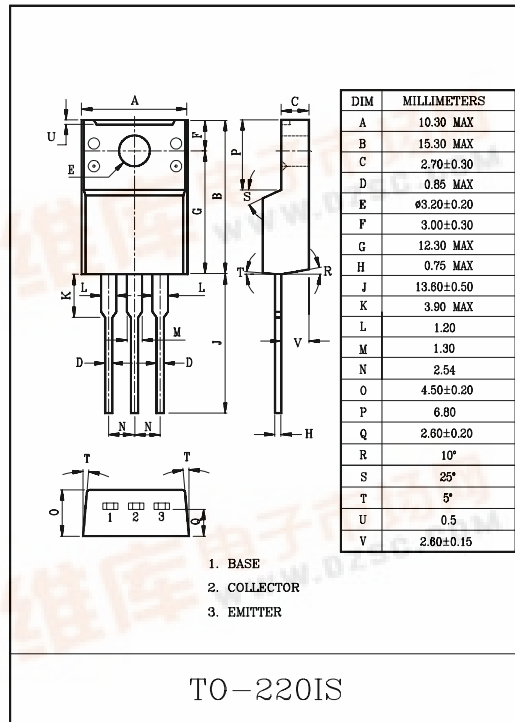
GENERAL PURPOSE APPLICATION.

FEATURES

- Good Linearity of h_{FE} .
- Complementary to KTC4369.

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-3	A
Base Current	I_B	-0.3	A
Collector Power Dissipation ($T_c=25^\circ\text{C}$)	P_C	15	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-20\text{V}, I_E=0$	-	-	-1.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$	-	-	-1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-30	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=-2\text{V}, I_C=-0.5\text{A}$	70	-	240	
	$h_{FE(2)}$	$V_{CE}=-2\text{V}, I_C=-2.5\text{A}$	25	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-2\text{A}, I_B=-0.2\text{A}$	-	-0.3	-0.8	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-2\text{V}, I_C=-0.5\text{A}$	-	-0.75	-1.0	V
Transition Frequency	f_T	$V_{CE}=-2\text{V}, I_C=-0.5\text{A}$	-	100	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$	-	40	-	pF

Note : $h_{FE(1)}$ Classification O:70~140 , Y:120~240